

# 2SB1001

# Silicon PNP Epitaxial

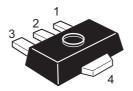
REJ03G0659-0200 (Previous ADE-208-1034) Rev.2.00 Aug.10.2005

### **Application**

- Low frequency power amplifier
- Complementary pair with 2SD1367

### **Outline**

RENESAS Package code: PLZZ0004CA-A (Package name: UPAK  $^{\circledR}$ )



- 1. Base
- 2. Collector
- 3. Emitter
- 4. Collector (Flange)

\*UPAK is a trademark of Renesas Technology Corp.

## **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

| Item                         | Symbol                              | Ratings     | Unit |
|------------------------------|-------------------------------------|-------------|------|
| Collector to base voltage    | V <sub>CBO</sub>                    | -20         | V    |
| Collector to emitter voltage | V <sub>CEO</sub>                    | -16         | V    |
| Emitter to base voltage      | V <sub>EBO</sub>                    | -6          | V    |
| Collector current            | Ic                                  | -2          | Α    |
| Collector peak current       | i <sub>C(peak)</sub> * <sup>1</sup> | -3          | Α    |
| Collector power dissipation  | P <sub>C</sub> * <sup>2</sup>       | 1           | W    |
| Junction temperature         | Tj                                  | 150         | °C   |
| Storage temperature          | Tstg                                | -55 to +150 | °C   |

Notes: 1. PW  $\leq$  10 ms, Duty cycle  $\leq$  20%

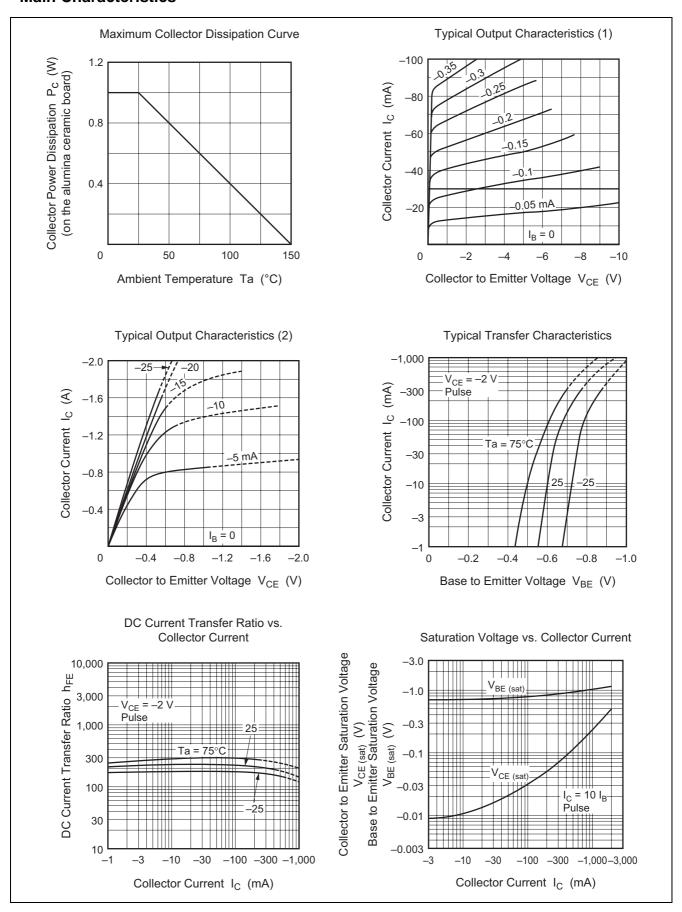
2. Value on the alumina ceramic board (12.5  $\times$  20  $\times$  0.7 mm)

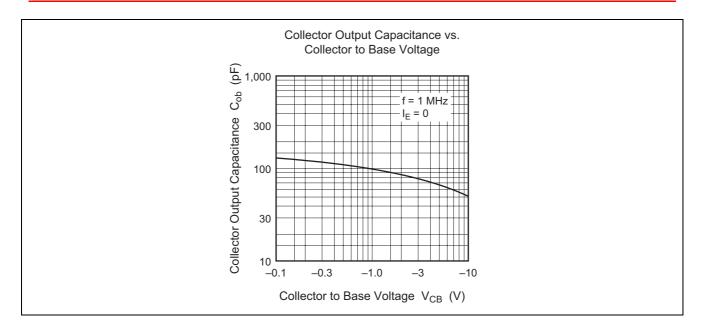
## **Electrical Characteristics**

 $(Ta = 25^{\circ}C)$ 

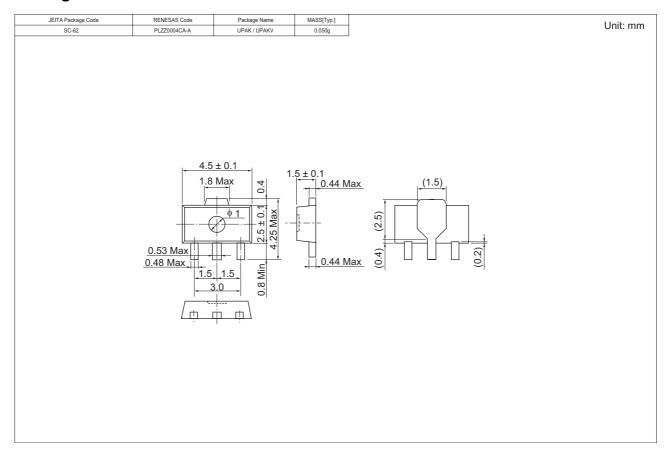
| Item                                    | Symbol           | Min | Тур   | Max  | Unit | Test conditions                        |
|---|------------------|-----|-------|------|------|--|
| Collector to base breakdown voltage     | $V_{(BR)CBO}$    | -20 | _     | _    | V    | $I_C = -10 \mu A, I_E = 0$             |
| Collector to emitter breakdown voltage  | $V_{(BR)CEO}$    | -16 | _     |      | V    | $I_C = -1 \text{ mA}, R_{BE} = \infty$ |
| Emitter to base breakdown voltage       | $V_{(BR)EBO}$    | -6  | _     |      | V    | $I_E = -10 \ \mu A, \ I_C = 0$         |
| Collector cutoff current                | I <sub>CBO</sub> |     | _     | -0.1 | μΑ   | $V_{CB} = -16 \text{ V}, I_E = 0$      |
| Emitter cutoff current                  | I <sub>EBO</sub> | _   | _     | -0.1 | μΑ   | $V_{EB} = -5 \text{ V}, I_C = 0$       |
| DC current transfer ratio               | h <sub>FE</sub>  | 160 | _     | 320  |      | V <sub>CE</sub> = −2 V,                |
|   |                  |     |       |      |      | $I_C = -0.1 \text{ A (Pulse test)}$    |
| Collector to emitter saturation voltage | $V_{CE(sat)}$    | _   | -0.15 | -0.3 | V    | $I_C = -1 A$ ,                         |
|   |                  |     |       |      |      | $I_B = -0.1 \text{ A (Pulse test)}$    |
| Base to emitter saturation voltage      | $V_{BE(sat)}$    | _   | -1.0  | -1.2 | V    | $I_C = -1 A$ ,                         |
|   |                  |     |       |      |      | $I_B = -0.1 \text{ A (Pulse test)}$    |
| Gain bandwidth product                  | f⊤               | _   | 150   | _    | MHz  | $V_{CE} = -2 V$ ,                      |
|   |                  |     |       |      |      | $I_C = -10 \text{ mA}$                 |
| Collector output capacitance            | Cob              | _   | 50    | _    | pF   | $V_{CB} = -10 \text{ V}, I_E = 0,$     |
|   |                  |     |       |      |      | f = 1 MHz                              |

### **Main Characteristics**





## **Package Dimensions**



## **Ordering Information**

| Part Name     | Quantity | Shipping Container                 |
|---------------|----------|------------------------------------|
| 2SB1001BJTR-E | 1000     | φ 178 mm Reel, 12 mm Emboss Taping |

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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